



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/796,111
				Filing Date	March 20, 2004
				First Named Inventor	Dean A. Klein
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0959/P959

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
PL	AA	US-6,673,648	01/06/2004	Lowrey	

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
1						

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

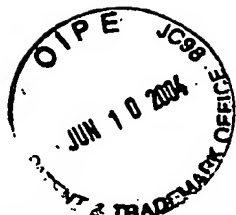
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Examiner: A H O M. Luy

Date: 10/28/04

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PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	10/796,111	
			Filing Date	March 10, 2004	
			First Named Inventor	Dean A. Klein	
			Art Unit	2818	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	13	Attorney Docket Number	M4065.0959/P0959

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
pl	AA	2002/0000666	1/2002	Kozicki et al.	
	AB	2002/0072188	6/2002	Gilton	
	AC	2002/0106849	08/2002	Moore	
	AD	2002/0123169	09/2002	Moore et al.	
	AE	2002/0123170	09/2002	Moore et al.	
	AF	2002/0123248	09/2002	Moore et al.	
	AG	2002/0127886	09/2002	Moore et al.	
	AH	2002/0132417	09/2002	Li	
	AI	2002/0160551	10/2002	Harshfield	
	AJ	2002/0163828	11/2002	Krieger et al.	
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	AM	2003/0001229	01/2003	Moore et al.	
	AN	2003/0027416	02/2003	Moore	
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	AQ	2003/0043631	03/2003	Gilton et al.	
	AR	2003/0045049	03/2003	Campbell et al.	
	AS	2003/0045054	03/2003	Campbell et al.	
	AT	2003/0047765	03/2003	Campbell	
	AU	2003/0047772	03/2003	Li	
	AV	2003/0047773	03/2003	Li	
	AW	2003/0049912	03/2003	Campbell et al.	
	AX	2003/0068861	04/2003	Li	
	AY	2003/0068862	04/2003	Li	
	AZ	2003/0095426	05/2003	Hush et al.	
	AA1	2003/0096497	05/2003	Moore et al.	
	AB1	2003/0107105	06/2003	Kozicki	
	AC1	2003/0117831	06/2003	Hush	
	AD1	2003/0128612	07/2003	Moore et al.	
	AE1	2003/0137869	07/2003	Kozicki	
	AF1	2003/0143782	07/2003	Gilton et al.	
	AG1	2003/0155589	08/2003	Campbell et al.	
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	AI1	2003/0156447	08/2003	Kozicki	
	AJ1	2003/0156463	08/2003	Casper et al.	
	AK1	2003/0209728	11/2003	Kozicki et al.	
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	AN1	3,622,319	11/1971	Sharp	
	AO1	3,743,847	7/1973	Boland	
	AP1	4,269,935	5/1981	Masters et al.	
	AQ1	4,312,938	1/1982	Drexler, et al.	
	AR1	4,316,946	1/1982	Masters, et al.	

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		<b>Complete If Known</b>			
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		Filing Date	March 10, 2004		
		First Named Inventor	Dean A. Klein		
		Art Unit	2818		
		Examiner Name	Not Yet Assigned		
Sheet	2	of	13	Attorney Docket Number	M4065.0959/P0959

PL	AS1	4,320,191	3/1982	Yoshikawa et al.	
	AT1	4,405,710	9/1983	Balasubramanyam et al.	
	AU1	4,419,421	12/1983	Wichelhaus, et al.	
	AV1	4,499,557	2/1985	Holmberg et al.	
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	AA2	5,177,567	1/1993	Kiersy et al.	
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	AC2	5,238,862	8/1993	Blalock et al.	
	AD2	5,272,359	12/1993	Nagasubramanian et al.	
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	AJ2	5,512,328	4/1996	Yoshimura et al.	
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	AM2	5,751,012	5/1998	Wolstenholme et al.	
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	AO2	5,814,527	9/1998	Wolstenholme et al.	
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	AR2	5,846,889	12/1998	Harbison et al.	
	AS2	5,851,882	12/1998	Harshfield	
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	AV2	5,998,066	12/1999	Block et al.	
	AW2	6,031,287	2/2000	Harshfield	
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	AB3	6,143,604	11/2000	Chiang et al.	
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	AO3	6,423,628	7/2002	Li et al.	

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Sheet	3	of	13	Attorney Docket Number	M4065.0959/P0959

PL	AP3	6,440,837	8/2002	Harshfield	
	AQ3	6,469,364	10/2002	Kozicki	
	AR3	6,473,332	10/2002	Ignatiev et al.	
	AS3	US 2004/0035401	2/2004	Ramachandran et al.	
	AT3	US 2003/0212724	11/2003	Ovshinsky et al.	
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			First Named Inventor	Dean A. Klein	
			Art Unit	2818	
			Examiner Name	Not Yet Assigned	
Sheet	4	of	13	Attorney Docket Number	M4065.0959/P0959

PL	AM5	US 5,534,711	7/1996	Ovshinsky et al.	
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	AO5	US 5,536,947	7/1996	Klersy et al.	
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	AB6	US 6,339,544	1/2002	Chiang et al.	
	AC6	US 6,404,865	6/2002	Lowery et al.	
	AD6	US 6,429,064	8/2002	Wicker	
	AE6	US 6,437,383	8/2002	Xu	
	AF6	US 6,462,984	10/2002	Xu et al.	
	AG6	US 6,480,438	11/2002	Park	
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	AJ6	US 6,507,061	1/2003	Hudgens et al.	
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	AL6	US 6,511,867	1/2003	Lowery et al.	
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	AN6	US 6,514,805	2/2003	Xu et al.	
	AO6	US 6,531,373	3/2003	Gill et al.	
	AP6	US 6,534,781	3/2003	Dennison	
	AQ6	US 6,545,287	4/2003	Chiang	
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	AV6	US 6,567,293	5/2003	Lowery et al.	
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	AX6	US 6,570,784	5/2003	Lowery	
	AY6	US 6,576,921	6/2003	Lowery	
	AZ6	US 6,586,761	7/2003	Lowery	
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	AB7	US 6,590,807	7/2003	Lowery	
	AC7	US 6,593,176	7/2003	Dennison	
	AD7	US 6,597,009	7/2003	Wicker	
	AE7	US 6,605,527	8/2003	Dennison et al.	
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	AG7	US 6,621,095	9/2003	Chiang et al.	
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	AI7	US 6,642,102	11/2003	Xu	

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pl	AJ7	US 6,646,297	11/2003	Dennison	
	AK7	US 6,649,928	11/2003	Dennison	
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	AM7	US 6,671,710	12/2003	Ovshinsky et al.	
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	AO7	US 6,674,115	1/2004	Hudgens et al.	
	AP7	US 6,687,427	2/2004	Ramalingam et al.	
	AQ7	US 6,690,026	2/2004	Peterson	
	AR7	US 6,696,355	2/2004	Dennison	
	AS7	US 6,687,153	2/2004	Lowery	
	AT7	US 6,707,712	3/2004	Lowery	
V	AU7	US 6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)				
pl	BA	JP-56126916	10/1981	Akira et al.		
pl	BB	WO 97/48032	12/18/1997	Kozicki et al.		
pl	BC	WO 99/28914	06/10/1999	Kozicki et al.		
Examiner Signature	D.H. M. Luu			Date Considered	10/22/04	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/618,824 796-111
		Filing Date	July 14, 2003
		First Named Inventor	Terry L. Gilton
		Group Art Unit	N/A
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	M4065.1006/P1006-A
Sheet	6	of	13

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PL	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Affifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).	
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		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
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				Attorney Docket Number	M4065.1006/P1006-A
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Examiner Signature	PHO M. Luy	Date Considered	10/23/24
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